

PATENT ABSTRACTS OF JAPAN

(11) Publication number: 08-245880

(43) Date of publication of application: 24.09.1996

(51) Int.CI. C08L 83/00

// C08G 77/62

(21) Application number: 07-079644 (71) Applicant: TONEN CORP

(22) Date of filing: 10.03.1995 (72) Inventor: TASHIRO YUJI

SUZUKI SUNAO

(54) HEAT-RESISTANT FILM AND ITS PRODUCTION

(57) Abstract:

PURPOSE: To obtain a highly heat-resistant film by forming a silicon copolymer comprising structural units represented by specific formulas into a film.

CONSTITUTION: A silicon copolymer having structural units represented by formulas I to V (wherein R1 and R2 are each alkyl, cycloalkyl, etc.; R3 is alkylene, alkenylene, etc.; II, m, and n are each 1 or higher; and o and p are each 0 or a positive integer) is obtd. by dissolving a diamine (e.g. p-phenylenediamine) in a solvent (e.g. xylene) in an N₂ atmosphere, dissolving a disilyl compd. [e.g. an organohydrodihalosilane, an organodihalosilane, or 1, 4-bis(dimethylchlorosilyl)benzene] in the soln. under heating, adding an amine to the resulting soln. to capture hydrochloric acid generated by the reaction, cooling the soln. to about 30°C or lower, adding NH₃ to react it with unreacted halogenosilane, removing unreacted NH₃ after the reaction, filtering the soln. under pressure, and removing the solvent. The copolymer is formed into a film and cured at 200-500°C in an N₂ atmosphere to give a low-birefringence film having a refractive index of 1.45 or higher.

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LEGAL STATUS [Date of request for examination] 28.02.2002

[Date of sending the examiner's decision of rejection] 02.04.2004

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

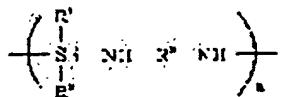
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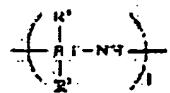


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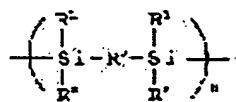
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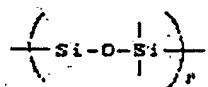
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III



IV



V

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